

# iscN-Channel MOSFET Transistor

## 2SK4115

RDS( • Enhand Vth = • 100% a • Minimu perform • DESCF • Switchi	ain-source on-resistance: $ON$ ) = 2.0 $\Omega$ (MAX) cement mode: = 2 to 4 V (V <sub>DS</sub> = 10 V, I <sub>D</sub> =1.0mA) avalanche tested Im Lot-to-Lot variations for robust de hance and reliable operation	I 2 3 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 3 0 0 0   I 0 0 0 0   I 0 0 0 0   I 0 0 0 0   I 0 0 0 0   I 0 0 0 0   I 0 0 0 0   I 0 0 0 0   I 0 0 0		
SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>DSS</sub>	Drain-Source Voltage	900	V	
$V_{GS}$	Gate-Source Voltage	±30	v	K ↓ G → ← L
Ι <sub>D</sub>	Drain Current-Continuous	7	A	→ ⊸ J → ⊸ D → ⊸ R → N→
I <sub>DM</sub>	Drain Current-Single Pulsed	21	A	DIM MIN MAX
P <sub>D</sub>	Total Dissipation @T <sub>c</sub> =25°C	150	w	A 19.60 20.30 B 15.50 15.70 C 4.70 4.90 D 0.90 1.10
Tj	Max. Operating Junction Temperature	150	°C	D 0.90 1.10 E 1.90 2.10 F 3.40 3.60 G 2.90 3.20
T <sub>stg</sub>	Storage Temperature	-55~150	°C	H 3.20 3.40 J 0.595 0.605 K 19.80 20.70
• THERM		L 1.90 2.20 N 10.89 10.91 Q 4.90 5.10		
SYMBOL	PARAMETER	МАХ	UNIT	R 3.35 3.45 S 1.995 2.100
Rth(ch-c)	Channel-to-case thermal resistance	0.833	°C/W	U 5.90 6.20 Y 9.90 10.10

isc website: www.iscsemi.cn

<sup>1</sup> isc & iscsemi is registered trademark



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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\texttt{C}}\text{=}25^{\circ}\!\!\!\mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 10mA	800			V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> = 10V; I <sub>D</sub> =1.0mA	2		4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =3.5A			2.0	Ω
lgss	Gate-Source Leakage Current	V <sub>GS</sub> = ±25V;V <sub>DS</sub> = 0V			±10	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =720V; V <sub>GS</sub> = 0V			100	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>DR</sub> =7A, V <sub>GS</sub> = 0 V			1.7	V



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